

Vishay Siliconix

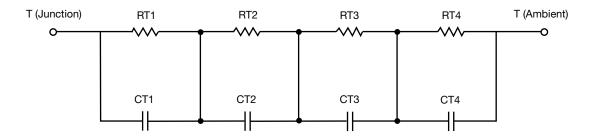
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in PSpice, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the PSpice simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the PSpice Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION THERMAL RESISTANCE (°C/W)					
RT1	n/a	153.2584m	n/a		
RT2	n/a	181.5421m	n/a		
RT3	n/a	136.8312m	n/a		
RT4	n/a	28.3683m	n/a		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	n/a	147.3650m	n/a		
CT2	n/a	167.8770m	n/a		
CT3	n/a	32.3620m	n/a		
CT4	n/a	19.5889m	n/a		

Note

• n/a indicates not applicable

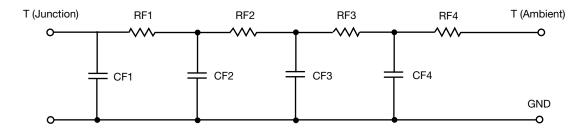
This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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R-C THERMAL MODEL FOR FILTER CONFIGURATION



R-C VALUES FOR FILTER CONFIGURATION THERMAL RESISTANCE (°C/W)					
RF1	n/a	89.6320m	n/a		
RF2	n/a	175.9244m	n/a		
RF3	n/a	4.4605m	n/a		
RF4	n/a	229.9831m	n/a		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	n/a	11.5779m	n/a		
CF2	n/a	12.3451m	n/a		
CF3	n/a	81.9055m	n/a		
CF4	n/a	449.7699u	n/a		

Note

• n/a indicates not applicable

SiHB30N60E_RC

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